

PSMN016-100PS

N-channel 100V 16 m Ω standard level MOSFET in TO-220 Rev. 3 — 27 September 2011 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a TO220 packages qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I_D	drain current	$T_j = 25$ °C; $V_{GS} = 10$ V; see Figure 1	-	-	57	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	148	W
Tj	junction temperature		-55	-	175	°C
Static ch	aracteristics					
DOON	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 °C;$ see <u>Figure 12</u>	-	-	28.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	13	16	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 30 \text{ A}; V_{DS} = 50 \text{ V};$	-	15	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15	-	49	-	nC
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;}$ $I_D = 60 \text{ A; } V_{sup} \le 100 \text{ V;}$ unclamped; $R_{GS} = 50 \Omega$	-	-	101	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	nber Package		
	Name	Description	Version
PSMN016-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

ain-source voltage ain-gate voltage te-source voltage ain current ak drain current al power dissipation orage temperature	$T_j \ge 25$ °C; $T_j \le 175$ °C $T_j \le 175$ °C; $T_j \ge 25$ °C; $R_{GS} = 20$ k Ω $V_{GS} = 10$ V; $T_{mb} = 100$ °C; see Figure 1 $V_{GS} = 10$ V; $T_j = 25$ °C; see Figure 1 pulsed; $t_p \le 10$ µs; $T_{mb} = 25$ °C; see Figure 3 $T_{mb} = 25$ °C; see Figure 2	- -20 - - -	100 100 20 40 57 230 148	V V V A A A
te-source voltage ain current ak drain current al power dissipation	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u> V_{GS} = 10 V; T_j = 25 °C; see <u>Figure 1</u> pulsed; $t_p \le 10 \ \mu s$; T_{mb} = 25 °C; see <u>Figure 3</u>	-20 - - - -	20 40 57 230	V A A A
ain current eak drain current eal power dissipation	$V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{pulsed}}; t_p \le 10 \text{ µs}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 3}}{\text{Figure 3}}$	- - -	40 57 230	A A A
ak drain current al power dissipation	$V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{pulsed}}; t_p \le 10 \text{ µs}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 3}}{\text{Figure 3}}$	-	57 230	A A
al power dissipation	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	230	Α
al power dissipation	<u> </u>	-		
· ·	T _{mb} = 25 °C; see <u>Figure 2</u>		148	W
orage temperature				- •
		-55	175	°C
nction temperature		-55	175	°C
ak soldering temperature		-	260	°C
liode				
urce current	T _{mb} = 25 °C	-	57	Α
ak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	230	Α
gedness				
n-repetitive drain-source	$V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; I_D = 60 \text{ A};$ $V_{sup} \le 100 \text{ V}; unclamped; R_{GS} = 50 \Omega$	-	101	mJ
	urce current ak source current gedness	urce current $T_{mb} = 25 ^{\circ}\text{C}$ ak source current pulsed; $t_p \le 10 \mu\text{s}$; $T_{mb} = 25 ^{\circ}\text{C}$ gedness n-repetitive drain-source $V_{GS} = 10 \text{V}$; $T_{j(init)} = 25 ^{\circ}\text{C}$; $I_D = 60 \text{A}$;	urce current $T_{mb} = 25 ^{\circ}\text{C}$ - ak source current pulsed; $t_p \le 10 \mu\text{s}$; $T_{mb} = 25 ^{\circ}\text{C}$ - gedness n-repetitive drain-source $V_{GS} = 10 \text{V}$; $T_{j(init)} = 25 ^{\circ}\text{C}$; $I_D = 60 \text{A}$; -	urce current $T_{mb} = 25 ^{\circ}\text{C}$ - 57 ak source current pulsed; $t_p \le 10 \mu\text{s}$; $T_{mb} = 25 ^{\circ}\text{C}$ - 230 gedness n-repetitive drain-source $V_{GS} = 10 \text{V}$; $T_{j(init)} = 25 ^{\circ}\text{C}$; $I_D = 60 \text{A}$; - 101

PSMN016-100PS

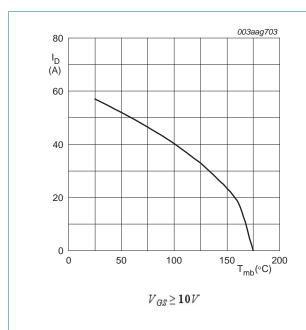


Fig 1. Continuous drain current as a function of mounting base temperature

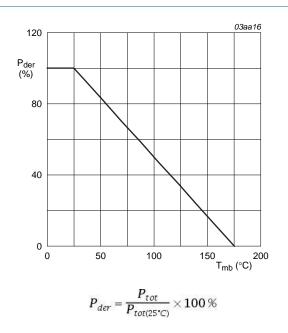
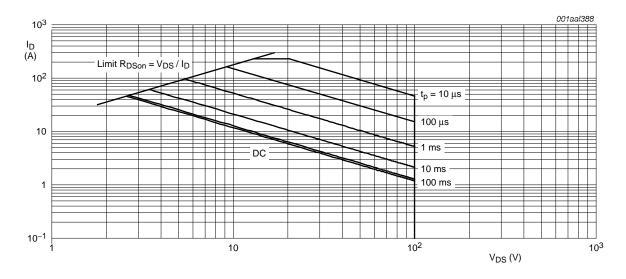


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.56	1.01	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		<u>[1]</u> _	50	-	K/W

[1] minimum footprint; mounted on a printed-circuit board to ambient

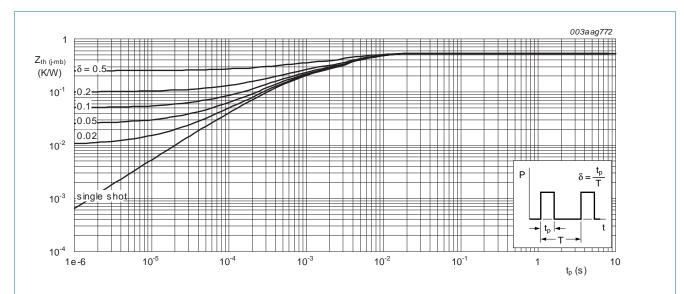


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see <u>Figure 10</u>	1	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	C 90 100 1 2 3 4 4.8 C - 100 - 100 - 100 - 10 100 - 10 100 - 10 100 - 10 100 - 10 100 - 10 100 - 128.8 - 36.4 44.8 - 13 16 - 0.9 40 49 12 7.75 4.25 15 4.5 2404 189 113 113 113 -	V		
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 10</u>	-	-	4.8	V
I_{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 125 °C	-	-	100	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	5	μΑ
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 12</u>	-	-	28.8	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 15 \text{ A; } T_j = 175 \text{ °C;}$ see Figure 12	5°C; - 13 16	44.8	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	13	16	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}$; $V_{DS} = 0 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14	-	40	-	nC
		see <u>Figure 14</u> $I_D = 30 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$;	-	49	-	nC
Q_{GS}	gate-source charge	see Figure 14; see Figure 15	-	12	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 30 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14	-	7.75	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	4.25	-	nC
Q_{GD}	gate-drain charge	$I_D = 30 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	15	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.5	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2404	-	pF
Coss	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	189	-	pF
C _{rss}	reverse transfer capacitance		-	113	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 1.7 \Omega; V_{GS} = 10 \text{ V};$	-	17	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 \text{ °C}$	-	23	-	ns
t _{d(off)}	turn-off delay time		-	36	-	ns
t _f	fall time		-	18	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	ain diode					
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$	-	54	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	126	-	nC

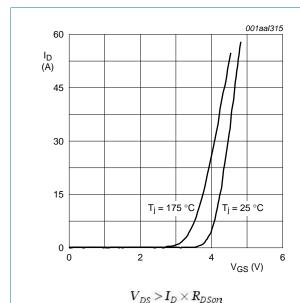


Fig 5. Transfer Characteristic: drain current as a function of gate-source voltage; typical values

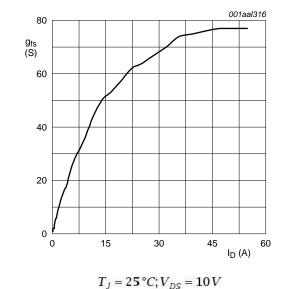


Fig 6. forward transconductance as a function of drain current; typical values

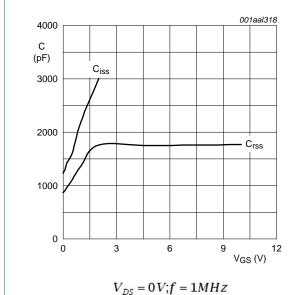
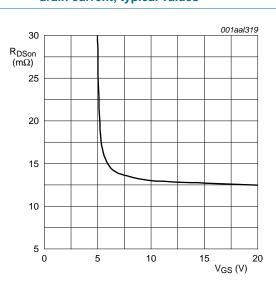


Fig 7. Input and revers transfer capacitances as a function of gate-source voltage; typical values



 $T_j = 25\,^{\circ}C; I_D = 5A$

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

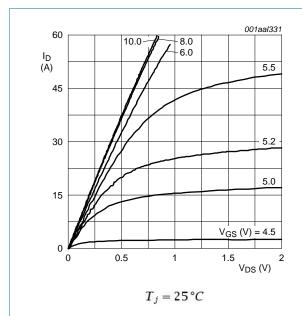


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

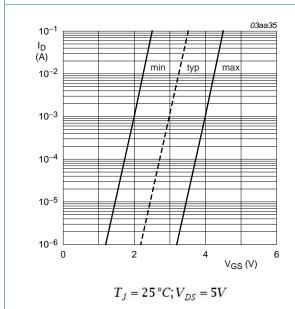
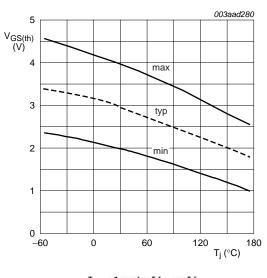


Fig 11. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

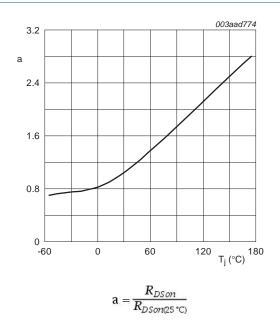


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

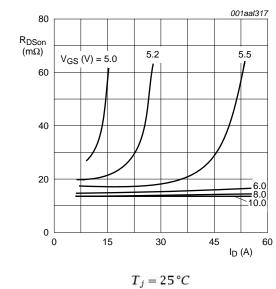


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

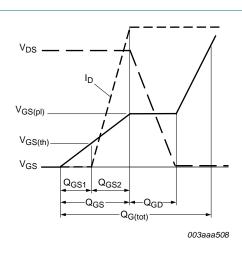
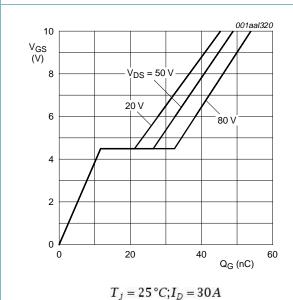
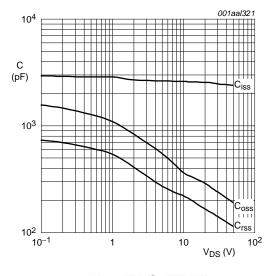


Fig 14. Gate charge waveform definitions



 $I_j = 23$ C, $I_D = 30$ A

Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

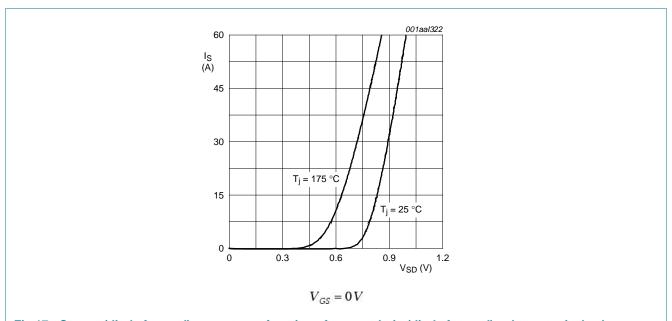
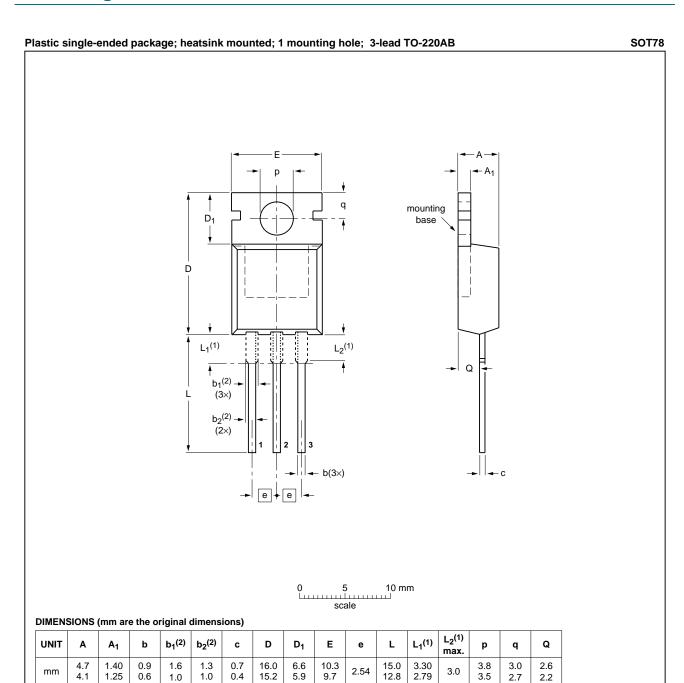


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig 18. Package outline SOT78 (TO-220AB)

PSMN016-100PS

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN016-100PS v.3	20110927	Product data sheet	-	PSMN016-100PS v.2
Modifications:	 Various changes to 	o content.		
PSMN016-100PS v.2	20110721	Product data sheet	-	PSMN016-100PS v.1

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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N-channel 100V 16 mΩ standard level MOSFET in TO-220

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PSMN016-100PS

N-channel 100V 16 m Ω standard level MOSFET in TO-220

11. Contents

1	Product profile	. 1
1.1	General description	. 1
1.2	Features and benefits	. 1
1.3	Applications	. 1
1.4	Quick reference data	. 1
2	Pinning information	. 2
3	Ordering information	.2
4	Limiting values	. 2
5	Thermal characteristics	.4
6	Characteristics	.5
7	Package outline	0
8	Revision history1	11
9	Legal information1	2
9.1	Data sheet status	2
9.2	Definitions1	2
9.3	Disclaimers	2
9.4	Trademarks1	
10	Contact information	12



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- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«**FORSTAR**» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели, кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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